

C3D03060E–Silicon Carbide Schottky Diode

Z-REC™ RECTIFIER

$$\begin{aligned} V_{RRM} &= 600 \text{ V} \\ I_{F(AVG)} &= 3 \text{ A} \\ Q_c &= 6.7 \text{ nC} \end{aligned}$$

Features

- 600-Volt Schottky Rectifier
- Optimized for PFC Boost Diode Application
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

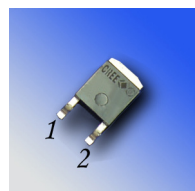
Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies
- Power Factor Correction
 - Typical PFC P_{out} : 300W-450W

Package



TO-252-2



Part Number	Package	Marking
C3D03060E	TO-252-2	C3D03060

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	600	V		
V_{RSM}	Surge Peak Reverse Voltage	600	V		
V_{DC}	DC Blocking Voltage	600	V		
$I_{F(AVG)}$	Average Forward Current	3.0	A	$T_c = 160^\circ\text{C}$	
I_{FRM}	Repetitive Peak Forward Surge Current	18 13.5	A	$T_c = 25^\circ\text{C}$, $t_p = 10 \text{ mS}$, Half Sine Wave $D = 0.3$ $T_c = 110^\circ\text{C}$, $t_p = 10 \text{ mS}$, Half Sine Wave $D = 0.3$	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	26 23	A	$T_c = 25^\circ\text{C}$, $t_p = 10 \text{ mS}$, Half Sine Wave $D = 0.3$ $T_c = 110^\circ\text{C}$, $t_p = 10 \text{ mS}$, Half Sine Wave $D = 0.3$	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	100	A	$T_c = 25^\circ\text{C}$, $t_p = 10 \mu\text{S}$, Pulse	
P_{tot}	Power Dissipation	53 23	W	$T_c = 25^\circ\text{C}$ $T_c = 110^\circ\text{C}$	
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage		1.7 2.4	V	$I_F = 3\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 3\text{ A}$ $T_J = 175^\circ\text{C}$	
I_R	Reverse Current	10 20	50 100	μA	$V_R = 600\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 600\text{ V}$ $T_J = 175^\circ\text{C}$	
Q_C	Total Capacitive Charge	6.7		nC	$V_R = 600\text{ V}$, $I_F = 3\text{ A}$ $di/dt = 500\text{ A}/\mu\text{S}$ $T_J = 25^\circ\text{C}$	
C	Total Capacitance	155 13 12		pF	$V_R = 0\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 200\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 400\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$	

Note:

1. This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit
$R_{\theta JC}$	TO-252 Package Thermal Resistance from Junction to Case	2.8	$^\circ\text{C}/\text{W}$

Typical Performance

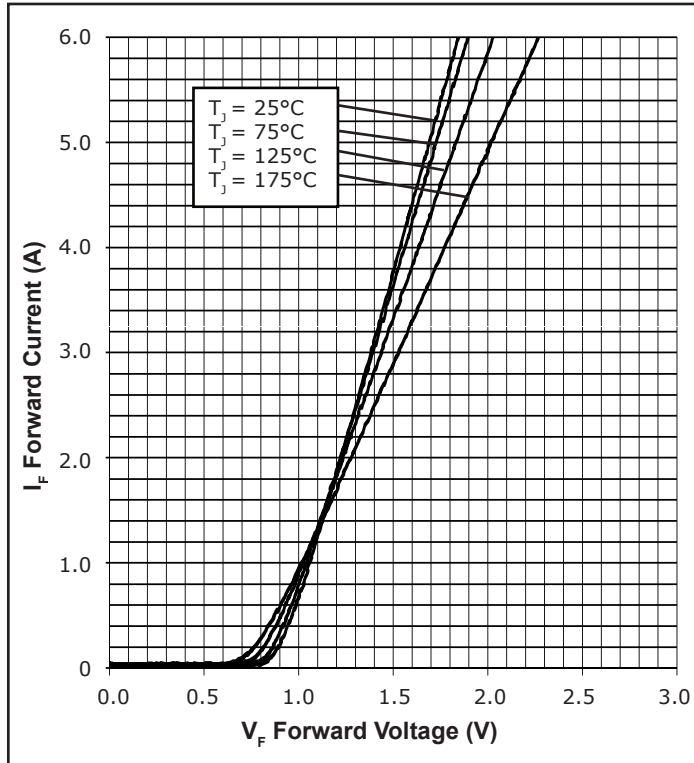


Figure 1. Forward Characteristics

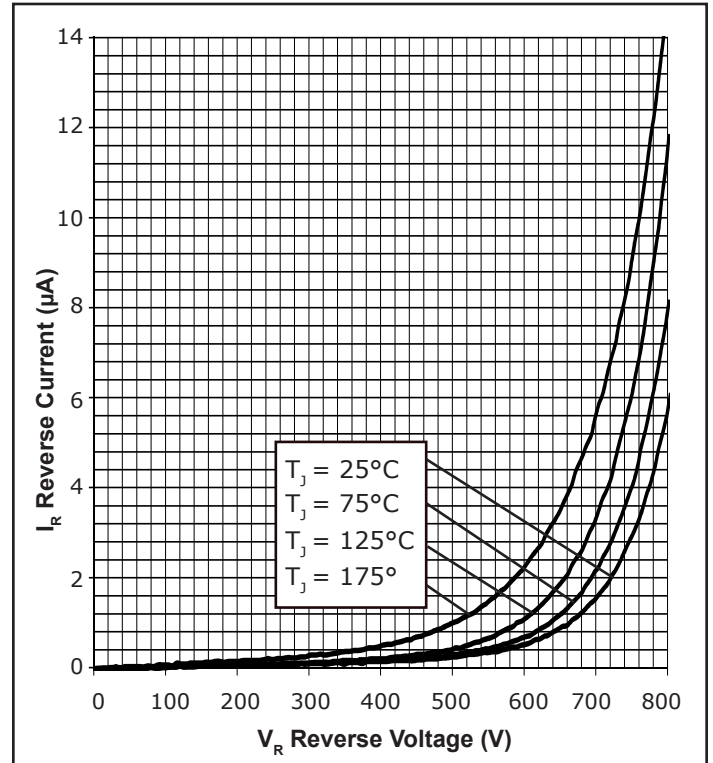


Figure 2. Reverse Characteristics

Typical Performance

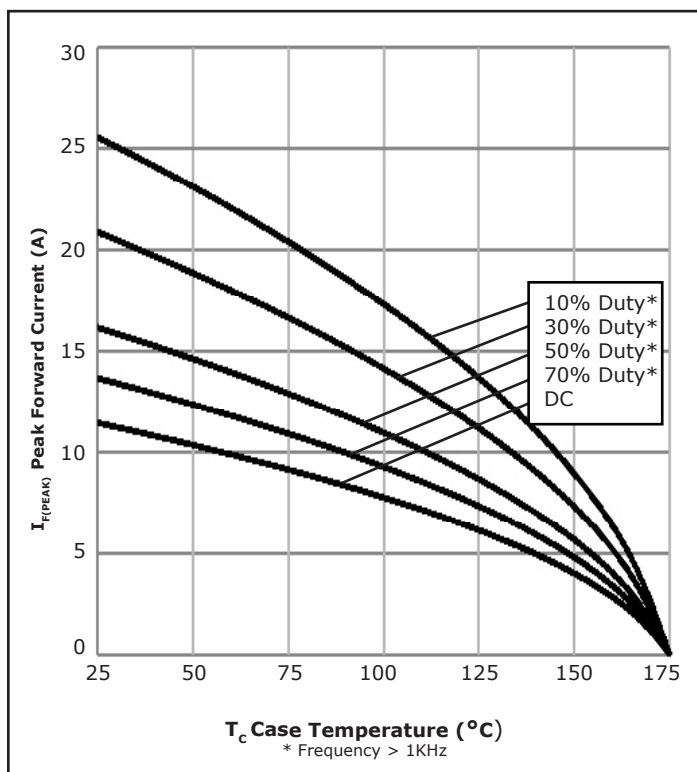


Figure 3. Current Derating

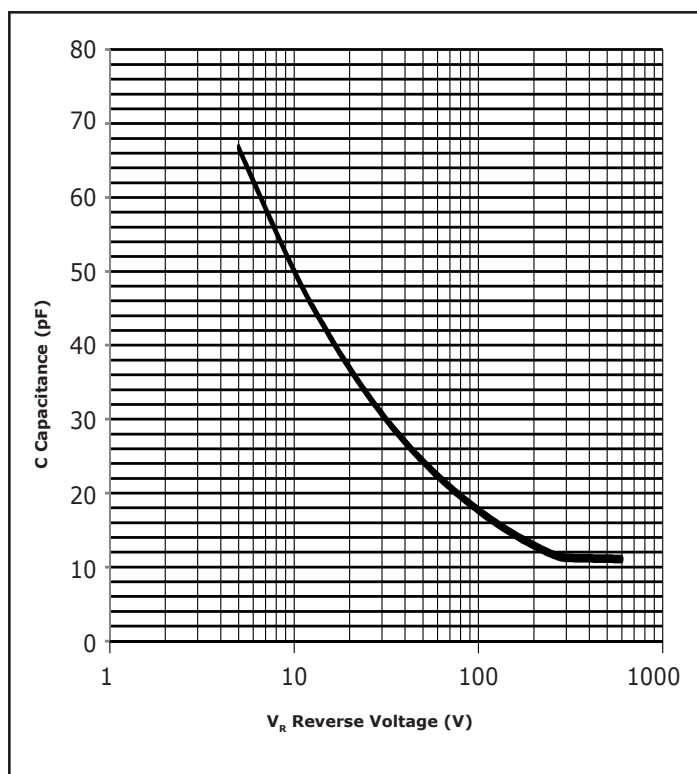


Figure 4. Capacitance vs. Reverse Voltage

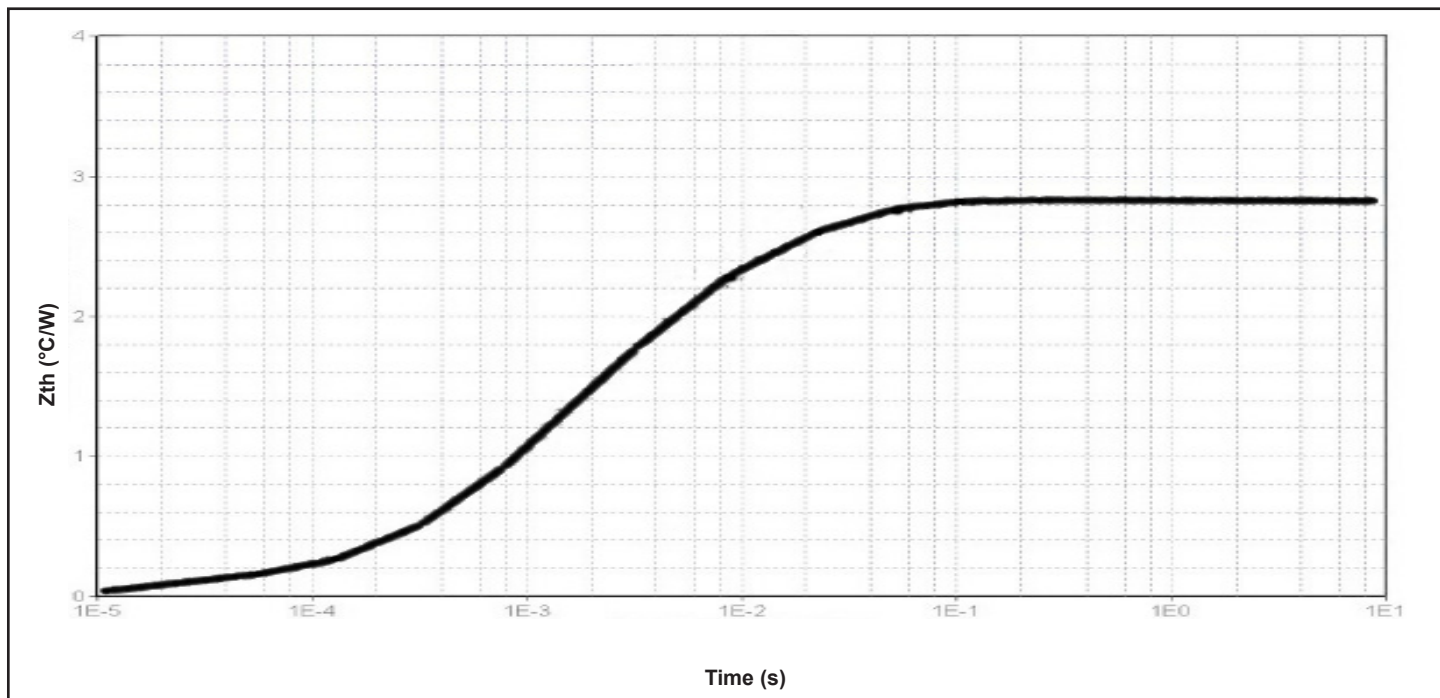


Figure 5. Transient Thermal Impedance

Typical Performance

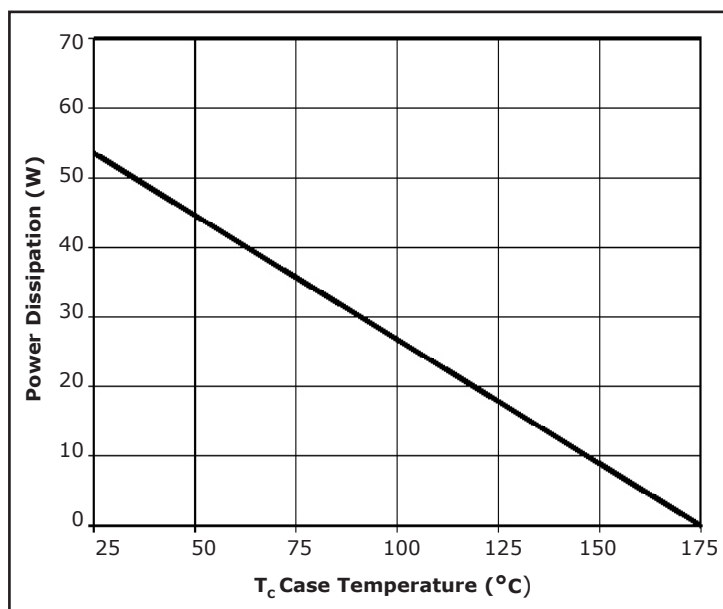
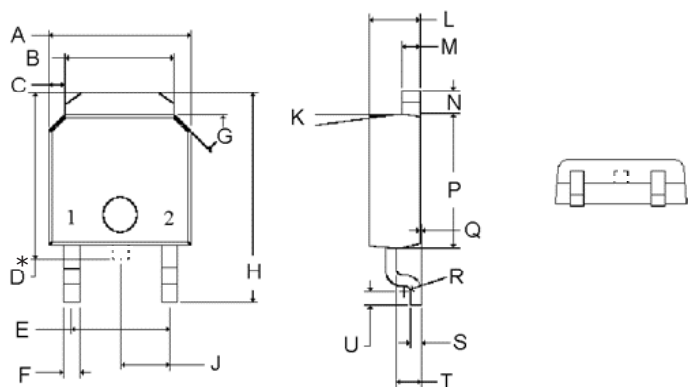


Figure 6. Power Derating

Package Dimensions

Package TO-252-2

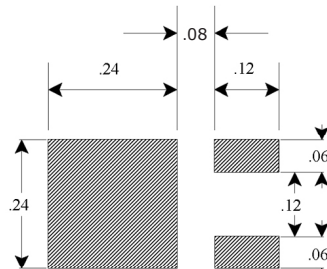


POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.250	.289	6.350	7.341
B	.197	.215	5.004	5.461
C	.027	.050	.686	1.270
D*	.270	.322	6.858	8.179
E	.178	.182	4.521	4.623
F	.025	.045	.635	1.143
G	44°	46°	44°	46°
H	.380	.410	9.652	10.414
J	.090 TYP		2.286 TYP	
K	6°	8°	6°	8°
L	.086	.094	2.184	2.388
M	.018	.034	.457	.864
N	.035	.050	.889	1.270
P	.231	.246	5.867	6.248
Q	0.00	.005	0.00	.127
R	R0.010 TYP		R0.254 TYP	
S	.017	.023	.432	.584
T	.038	.045	.965	1.143
U	.021	.029	.533	.737

Note:

* Tab "D" may not be present

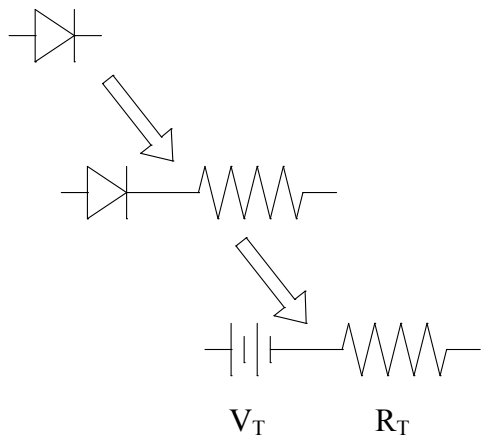
Recommended Solder Pad Layout



TO-252-2

Part Number	Package	Marking
C3D03060E	TO-252-2	C3D03060

Diode Model



$$V_T = V_T + I_f \cdot R_T$$

$$V_T = 1.01 + (T_j - 1.26 \cdot 10^{-3})$$

$$R_T = 0.14 + (T_j - 1.13 \cdot 10^{-3})$$

Note: T_j = Diode Junction Temperature In Degrees Celcius

"The levels of environmentally sensitive, persistent biologically toxic (PBT), persistent organic pollutants (POP), or otherwise restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2002/95/EC on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS), as amended through April 21, 2006.

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